

2N2322 2N2326
 2N2323 2N2327
 2N2324 2N2328
 2N2325 2N2329

**SILICON CONTROLLED RECTIFIER
 1.6 AMPS, 25 THRU 400 VOLTS**



TO-39 CASE

CentralTM Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N2322 Series types are hermetically sealed Silicon Controlled Rectifiers designed for sensing circuit applications and control systems.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	2N23__								UNITS
		<u>22</u>	<u>23</u>	<u>24</u>	<u>25</u>	<u>26</u>	<u>27</u>	<u>28</u>	<u>29</u>	
Peak Repetitive Forward Voltage	V_{DRM}	25	50	100	150	200	250	300	400	V
Peak Repetitive Reverse Voltage	V_{RRM}	25	50	100	150	200	250	300	400	V
Non-Repetitive Peak Reverse Voltage	V_{RSM}	40	75	150	225	300	350	400	500	V
RMS On-State Current	$I_T(\text{RMS})$					1.6				A
Average On-State Current ($T_C=85^\circ\text{C}$)	$I_T(\text{AV})$					1.0				A
Peak One Cycle Surge ($t=8.3\text{ms}$)	I_{TSM}					15				A
Peak Gate Power	P_{GM}					0.10				W
Average Gate Power	$P_{G(\text{AV})}$					0.01				W
Peak Gate Current	I_{GM}					0.10				A
Peak Gate Voltage	V_{GM}					6.0				V
Junction Temperature	T_J					-65 to +125				$^\circ\text{C}$
Storage Temperature	T_{stg}					-65 to +150				$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, R_{GK}=1.0\text{k}\Omega$		5.0	μA
I_{GT}	$V_D=6.0\text{V}, R_L=100\Omega$		200	μA
I_H	$V_D=6.0\text{V}, R_{GK}=1.0\text{k}\Omega$		2.0	mA
V_{GT}	$V_D=6.0\text{V}, R_L=100\Omega$		0.8	V
V_{TM}	$I_{TM}=1.0\text{A}, t_p=380\mu\text{s}$		1.5	V

